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Practical PV energy harvesting under real indoor lighting conditions

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8 ABSTRACT

9 Indoor light can be used as a new energy source to power µW low consumption wireless sensor networks (WSNs), but for wireless electronic devices consuming tens of mW, it is still challenging. 10 11 The challenge comes from the low level of irradiance and from the several kinds of source 12 combinations varying in time (multi-spectral direct, reflective, and scattered mix of artificial and 13 natural light). This article describes a simple and reliable method that provides a model-based 14 evaluation of the harvestable energy from any real indoor light environment. This method uses 'real 15 condition' indoor light spectral measurements with a spectrometer as well as 'controlled condition' 16 optoelectrical characteristics of the photovoltaic solar cells. The model-based evaluation of the 17 harvestable energy has been compared with real microsource prototypes based on commercial photovoltaic cells powering commercial wireless e-ink display (more than 10 mW consumption 18 19 averaged on a day). In this article, we show that it is possible to evaluate the harvestable energy, for 20 several days of indoor light exposure, with an error lower than 6 %. Our method, with such an 21 accuracy range, will be a helpful tool to assist engineers and researchers in designing light energy 22 harvesting systems and more generally could find wide application in the growing IoT ecosystem.

23

24 ARTICLE INFO

25 *Keywords:* Energy Harvesting; Calculation Model; Indoor Light; Indoor PV; Mixed Light; Real Life Conditions.

26 1. Introduction

The number of low-power wireless devices is increasing significantly, and as a result, there is more 27 28 and more research focusing on new ways to supply energy to these devices (Mathúna et al., 2008). 29 Indeed, the growth in energy demand induced by this new field of application poses unprecedented 30 challenges to provide the energy needed to operate these devices (Mathews et al., 2019). It also requires a review of how this energy is supplied and produced while minimizing its economic and 31 32 environmental impact. One practical approach investigated for this purpose is harvesting light energy 33 from the surroundings of the device. Past research has proven the viability of this approach in outdoor 34 environments (Shaikh and Zeadally, 2016). In an indoor environment, where radiated levels are low, 35 light energy harvesting has been identified as an effective method to provide enough power to low-

- 36 power electronic systems such
- as wireless sensor networks (Matiko et al., 2014). Moreover, harvesting energy from light has
- demonstrated its capability as a means to achieve battery-free applications (Brunelli et al., 2009; Wang
- et al., 2016).
- 40

However, when it comes to considering energy harvesting for indoor applications, the difficulty in 41 42 characterizing the harvestable power becomes substantial. Even though Standard Test Conditions 43 (STC) from IEC 60904-3 are not entirely representative of the behavior of photovoltaic (PV) 44 converters in real-life conditions, it is still a practical way to compare them. As for indoor conditions, the situation is somewhat different. The existing standards ISO 8995:2002 and CIE S 008/E define the 45 46 level of luminosity required depending on the task associated with a workplace. The unit of this appropriate luminosity level is given in a semi-empirical unit of measure called lux. The lux (or lumen 47 48 per m²) value E_{ν} is given by the following equation:

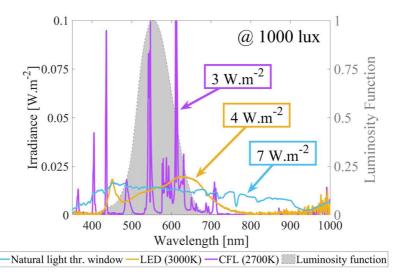
Nomenclature

a-Si:Hhydrogenated amorphous siliconLEDLight-Emitting DiodeCFLcompact fluorescent lightLi-PoLithium-Polymer η^{SQ} theoretical SQ solar cell efficiencyMAPEmean absolute percentage error η^{meas} measured solar cell efficiencyMPPTmaximum power point tracking E_g bandgap energy n diode's ideality factor EQE external quantum efficiencypc-Sipolycrystalline silicon E_v illuminancePCEpower conversion efficiency (PCE) FF^{SQ} theoretical fill factor from SQ model P_{ln} incident powerFOCVfractional open-circuit voltage P^{meas}_{max} measured power -voltageGaAsgalium arsenide P_{max}^{max} measured maximum powerhPlanck's constant $P^{mod}(V)$ calculated power -voltage $I_s^{Q_c}$ short circuit SQ current densityPMICpower management integrated circuit $I_s^{Q_c}$ short circuit SQ current densityRsparasitic series resistance $I_s^{Q_c}$ theoretical SQ saturation current densitySUUSource Meter Unit $I_{max}^{Q_c}(V)$ measured dark current density-voltageSQrelated to Shockley-Quiesser model $J_{sc}^{Q_c}$ short-circuit current density-voltageSQrelated to Shockley-Quiesser model $J_{max}^{Q_c}(V)$ estimated current density-voltageSQtheoretical SQ open-circuit voltage $J_{max}^{Q_c}$ short-circuit current density-voltageSQtheoretical SQ open-circ	Nomenciature				
$ \begin{array}{ccccc} & & \mbox{MAPE} & \mbox{mean absolute percentage error} \\ & & \mbox{meas} & \mbox{measured solar cell efficiency} & \mbox{MAPE} & \mbox{mean absolute percentage error} \\ & & \mbox{meas} & \mbox{measured solar cell efficiency} & \mbox{MPPT} & \mbox{maximum power point tracking} \\ & & \mbox{E}_g & \mbox{badga energy} & n & \mbox{diode's ideality factor} \\ & & \mbox{E}_g & \mbox{extral quantum efficiency} & \mbox{pc-Si} & \mbox{polycrystalline silicon} \\ & & \mbox{E}_v & \mbox{illuminance} & \mbox{PCE} & \mbox{power conversion efficiency} (PCE) \\ & & \mbox{freetical fill factor from SQ model} & P_{in} & \mbox{incident power} \\ & & \mbox{measured fill factor} & \mbox{freetical open-circuit voltage} & \mbox{pmeas} \\ & & \mbox{measured fill factor} & \mbox{open-circuit voltage} & \mbox{pmeas} \\ & & \mbox{measured fill actor} & \mbox{open-circuit voltage} & \mbox{pmeas} \\ & & \mbox{measured fill actor} & \mbox{open-circuit voltage} & \mbox{pmeas} \\ & & \mbox{measured fill marsenide} & \mbox{pmeas} \\ & & \mbox{measured maximum power} & \mbox{voltage} \\ & & \mbox{measured fill actor} & \mbox{pmeas} \\ & & \mbox{measured fill factor} & \mbox{measured fill factor} & \mbox{measured fill factor} \\ & & \mbox{measured fill factor} & \mbox{meas} \\ & & \mbox{measured fill factor} & \mbox{measured} & \mbox{measured fill factor} \\ & & \mbox{measured fill factor} & \mbox{meas} \\ & & \mbox{measured fill factor} & \mbox{measured} & \mbox{measured maximum power} \\ & & \mbox{measured fill factor} & \mbox{measured} & \mbox{measured maximum power} \\ & & \mbox{measured fill factor} & \mbox{measured fill factor} & \mbox{measured fill factor} \\$	a-Si:H	hydrogenated amorphous silicon	LED	Light-Emitting Diode	
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k Boltzmann's constant Y_{λ} photopic luminosity function	$J^{mod}(V)$	estimated current density-voltage (model)	V _{OC}	theoretical SQ open-circuit voltage	
	$J^{meas}(V).$	measured current density-voltage	WSN	wireless sensor network	
<i>K_{cd}</i> maximum spectral efficiency coefficient	k	Boltzmann's constant	Y_{λ}	photopic luminosity function	
	K _{cd}	maximum spectral efficiency coefficient			

$$E_{\nu} = K_{cd} \int_0^\infty I_{\lambda} Y_{\lambda} \ d\lambda \,, \tag{1}$$

where Y_{λ} is a function related to the human eye's cones sensitivity to light (shown in Fig. 1) also called the photopic luminosity function, I_{λ} is the irradiance and K_{cd} is a coefficient called maximum spectral efficiency, defined as 686 lux.W⁻¹.m⁻² in such a way that irradiance of 1000 W.m⁻² in standard condition (AM 1.5G) corresponds to 100 klux.

53 Nevertheless, when considering how much energy could be harvested from PV converters, the first 54 issue arises: the luminosity in lux is not a reliable quantification of the incident harvestable power (Wang et al., 2010). Indeed, as an example, Fig. 1 presents the emission spectra from 3 different light 55 sources: i) the natural light through a window, ii) a compact fluorescent light (CFL), and iii) a light-56 57 emitting diode (LED). The three spectra have been measured with a commercial calibrated 58 spectroradiometer, the StellarRAD from *StellarNet Inc.*, equipped with a CR2 cosine receptor with a wavelength range from 350 nm to 1100 nm, adapted to indoor environments. Spectra are set to obtain 59 a 1000 lux illuminance level, giving three different levels of irradiance for each light source: 7 W.m⁻² 60 for natural light through the window, 3 W.m⁻² for the CFL source, and 4 W.m⁻² for the LED source. 61



62

Fig. 1. Typical 1000 lux single source indoor environment light spectra: a 3000K LED bulb (in blue), a 2700K CFL bulb (in yellow), and natural light through a window (in red). In green, the luminosity function Y_{λ} used to establish the illuminance level (lux).

In addition, there is a second problem. In the case of real indoor lighting, the incident radiation is a 66 time-varying mixture of multiple natural and artificial direct, reflective, and scattered sources: it has to 67 68 be taken into account to have a reliable estimation of the photovoltaic cell performance based on real 69 indoor light illumination (Li et al., 2015; Ma et al., 2017; Minnaert and Veelaert, 2014a; Sacco et al., 70 2013). Finally, the third issue is technological. Indeed, the PV converters are non-ideal devices connected to a non-ideal electrical storage device via a non-ideal power management integrated circuit 71 72 (PMIC) devices. It means that the electrical energy received by the final consumer device is 73 technology dependent and should be far from the standard theoretical Shockley-Queisser (SQ) limit 74 model predictions (Shockley and Queisser, 1961), whatever the relaxing assumption of the SQ model 75 taken into account (Guillemoles et al., 2019). In the last few years, many researchers have been 76 focused on overcoming these challenges to reach a reliable valuation of the harvestable surrounding 77 low light energy, for example by optimizing the one diode photovoltaic model parameter or new 78 experimental methods for indoor applications (Bader et al., 2019; Fajardo Jaimes and Rangel de 79 Sousa, 2017; Ma et al., 2020; Masoudinejad et al., 2016). But in each of these studies, only the case of 80 controlled mono artificial sources is considered.

81 In this article, we present a methodology that allows estimating the harvestable energy from any 82 real indoor varying light environment. The first part will present a standard model based on SQ and 83 compare it to some usual real-life PV converters. The second part will present a calculation model based on experimental data focusing mainly on a commercial flexible thin-film Gallium-Arsenide 84 (GaAs) PV solar cell from Alta Devices Inc. (Kayes et al., 2011) under several controlled single 85 sources of light. Finally, the third part will present an energy harvesting system prototype based on the 86 GaAs solar cell, working for several days in real varying indoor environments. It is to be noted that 87 this prototype is the micro source of a classic wireless e-ink wifi connected device, with an average 88 89 power consumption of around 10 mW.

90 2. The Shockley-Queisser limit theoretical model adapted to indoor light energy harvesting

During the last decade, several studies have been conducted to compare the performance of different PV technologies under controlled artificial indoor light single sources (Apostolou et al., 2016; Carvalho and Paulino, 2014; De Rossi et al., 2015; Kasemann et al., 2014; Li et al., 2015; Minnaert and Veelaert, 2014b; Müller et al., 2009). Trying to face the complex task of choosing the best technology to use when dealing with indoor light-harvesting, there is an attractive approach that consists in applying the SQ limit model. This model gives the theoretical maximum conversion efficiency η^{SQ} for an ideal semiconductor single-junction solar cell at any theoretical bandgap:

$$\eta^{SQ}(E_g) = \frac{V_{OC}^{SQ} J_{SC}^{SQ} FF^{SQ}}{P_{in}},\tag{2}$$

with P_{in} the incident power depending on the spectrum composition, V_{oc}^{SQ} the ideal SQ open-circuit voltage of the PV converter, J_{Sc}^{SQ} the ideal SQ short circuit current and FF^{SQ} the ideal SQ fill-factor. In the case of an ideal semiconductor, the short-circuit current equals the photocurrent J_{ph}^{SQ} , which is related to the number of incident photons carrying more energy than the bandgap E_a :

$$J_{SC}^{SQ} = J_{ph}^{SQ} = q \int_0^{\lambda_g} \Phi_{p,\lambda} \, d\lambda \,, \tag{3}$$

102 Where $\Phi_{p,\lambda}$ is the incident photon flow at each optical wavelength λ , q the elementary electric 103 charge, and λ_g the wavelength corresponding to the considered bandgap E_g . 104 The ideal SQ fill factor FF^{SQ} can be found following the semi-empirical model from Green's 105 approximation (Green and Hall, 1982):

$$FF^{SQ} = \frac{\left[\frac{qV_{OC}^{SQ}}{kT} - ln\left(\frac{qV_{OC}^{SQ}}{kT} + 0.72\right)\right]}{\left(\frac{qV_{OC}^{SQ}}{kT} + 1\right)}$$
(4)

106 with *k* being the Boltzmann's constant and *T* the device's temperature. The PV cell open-circuit 107 voltage V_{OC} can be defined by the following equation, in the case of an ideality factor *n* equal to 1:

$$V_{OC}^{SQ} = \frac{kT}{q} \times ln \left(\frac{J_{ph}^{SQ}}{J_0^{SQ}} + 1 \right).$$
(5)

Finally, the ideal theoretical dark current density saturation J_0^{SQ} in a single junction is given by (Shockley and Queisser, 1961) and (Müller et al., 2013):

$$J_0^{SQ} = qA \frac{2\pi kT}{h^3 c^2} (E_g + kT)^2 e^{\frac{-E_g}{kT}}$$
(6)

with *A* the active surface area of the PV converter, *h* the Planck's constant, and *c* the speed of light invacuum.

This SQ model is mostly known for having predicted the famous limit efficiency of 33 % for an 112 ideal bandgap around 1.14 eV under the standard (AM 1.5G) sun radiation (Shockley and Queisser, 113 114 1961). However, it can also be applied to any kind of spectra like one of the indoor light environments (Müller et al., 2013). For example, Fig. 2(a) shows the result of the SQ model when 115 116 applied to typical indoor environments, identical to those in Fig. 1, each with an illuminance of 1000 117 lux. As expected, theoretical efficiencies depend on the spectrum composition and on the fact that the 118 ideal bandgap changes from one single source to another. As a result of this application of the SQ 119 model, for any indoor light, the model gives theoretical efficiency much higher than the solar STC 120 AM1.5G spectrum. In the case of a CFL source, with a theoretical semiconductor with a bandgap around $E_q = 1.95$ eV, an efficiency as high as $\eta^{SQ}(E_q) = 54$ % is predicted. 121

To compare the SQ limit theory to experimental measurement, a commercial source-meter unit 122 (SMU), 2450 from Keithley, has been used to measure $J^{meas}(V)$: the current density-voltage 123 characteristics of different PV converters made of different technologies: hydrogenated amorphous 124 125 silicon (a-Si:H) solar cell (panel) from Xiamen Mars Rock Science Technology Co., a gallium-arsenide 126 (GaAs) mono-junction flexible PV solar cell from Alta Devices Inc. (Kayes et al., 2011), and a polycrystalline silicon (pc-Si) solar cell from SEEEDSTUDIO, in controlled indoor single source 127 environments, with different levels of irradiance. The results of the measured fill-factor FF^{meas} 128 extracted from the $I^{meas}(V)$ curves, as well as the FF^{SQ} are plotted in Fig. 2(b). 129

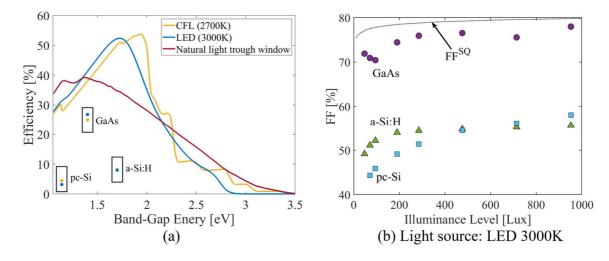


Fig. 2. (a) Theoretical maximum conversion efficiency $\eta^{SQ}(E_g)$ of a single ideal p-n junction based on the SQ model for different single sources: CFL, LED, and natural light through a window. Dots are the measured efficiency of different PV converters technology under CFL and LED at around 500 lux. (b) Experimentally measured Fill-factor FF^{meas} of commercial solar cells (GaAs, a-S:H and pc-Si) and their evolution versus LED light intensity. As a comparison, an ideal solar cell FF^{SQ} based on the SQ model is shown in plain black.

130

The efficiency conversion of the different commercial PV converters technologies is, as expected, 136 different in real conditions from what has been theoretically predicted by the SQ model. It is mostly 137 attributed to several losses, such as shadowing, series and shunt resistance, ideality factor, optical 138 139 absorption, semiconductor quality, low mobility, small minority carrier lifetime, and the PV 140 converters' fill-factors and thus efficiencies decreasing at low light intensity (Randall and Jacot, 2003). Indeed, J_{ph}^{SQ} varies linearly with the light intensity (3), V_{OC}^{SQ} depends on J_{ph}^{SQ} (5) and FF^{SQ} depends on 141 V_{OC}^{SQ} (4). As an example, the theoretical fill-factor based on the SQ model is shown in Fig .2(b) for a 142 theoretical bandgap corresponding to the standard technologies for indoor application (a-Si:H, pc-Si, 143 and GaAs) and illuminance (from 100 to 1000 lux) with a LED single source. When comparing the 144 experimental results of three commercial PV converters while varying the light intensity of a LED 145 bulb, it can be seen that the fill-factor decreases with lower light intensity, as it is forecast by the 146 theoretical FF equation, but with a more dramatic decrease. Indeed, the experimental FF^{meas} of the 147 148 pc-Si cell strongly decreases when reducing the light intensity, mainly due to their too low shunt 149 resistance (Reich et al., 2009). Thus, as reported previously and exposed in Fig. 2(b), the c-Si 150 technology is not the most suitable technology for indoor applications, and therefore not a good 151 candidate for developing a model based on a one-diode photovoltaic model where the FF needs to 152 vary as little as possible. The a-Si:H and GaAs technologies have a more stable FF from 100 to 1000 lux, which seems ideal for the simple model presented. Nevertheless, the FF of the a-Si:H PV 153 converter is lower than the GaAs cell, and thus its power conversion efficiency (PCE) η^{meas} tends to 154 155 indicate less promising model performance. For indoor applications, especially when dealing with 156 consumer devices with an average consumption of 10 mW, a technology that does not suffer from a low level of light, but also that has a FF and a PCE close their ideal value is needed. As seen in Fig. 157 2(b), only the GaAs cells have demonstrated such good performances, with a measured FF closer to 158 159 the FF of the Shockley-Queisser model of an ideal solar cell than other considered cells: this is not 160 surprising since III-V solar cells are known to be among the most efficient cells, even under low indoor light conditions (Mathews et al., 2016). This difference in performance is mainly due to the 161 162 known fact that the carrier mobility is high and the lifetime long in GaAs devices (Kayes et al., 2011), that the series resistance is low enough, and the shunt resistance high enough to avoid deviation of the 163 FF, even in a low light environment. In conclusion, the fact that the experimental FF^{meas} is almost 164 constant under an illuminance ranging from 100 to 1000 lux considerably simplifies the theoretical 165 166 calculation of the output power of a GaAs PV cell from any spectrum, by safely applying the 167 superposition model, even at a low light intensity.

168 The next paragraph will describe a methodology based on the superposition model to predict the 169 extractable energy from the GaAs thin-film solar cell, whatever the real indoor light source 170 environment.

171 3. A calculation model of indoor light energy harvesting based on a one-diode photovoltaic model

The method is based on the combination of the results from three measurements: i) the light 172 environment spectrum (which is fluctuating in time), ii) the external quantum efficiency (EQE) of the 173 174 PV cell (unchanging intrinsic values) and iii) the measurement of the current density-voltage $J_{dark}^{meas}(V)$ characteristic in the dark (unchanging intrinsic values). This simple methodology allows us to consider 175 the primary deviations from the SQ model: a real EQE instead of an ideal one over the whole range of 176 the spectra, and a real $J_{dark}^{meas}(V)$ curve, which takes into account the real "shape" (FF) of the current 177 density -voltage J(V) characteristic, including the parasitic series R_s and shunt R_{sh} resistances as well 178 179 as the ideality factor n, which can vary from 1 to 2. The spectral response was measured with a 180 custom-built setup composed of a Xenon lamp, a monochromator equipped with two diffraction 181 gratings, a filter wheel to remove the higher diffraction orders of radiation, and a lock-in amplifier. The 182 measurements were calibrated with Si and Ge photodiodes (Thorlabs FDS100-CAL and FDG03-CAL, 183 respectively) to cover the whole wavelength range of interest. This characterization does not consider 184 the impact of the solid angle of the radiation. It studies the characteristics of the PV converter with a photon flow that is normal to its surface. For each wavelength band produced by the source, the current 185 generated by the characterized PV cell is measured. A known cell is used as a current-generation 186 reference to establish the EQE of the characterized PV cell by comparison. 187

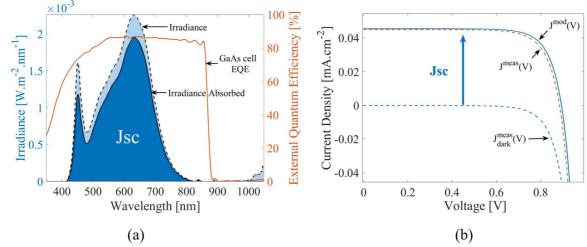
188 In the developed model, the measured *EQE* is added in (3) to consider the deviation from the SQ 189 model due to the real external quantum efficiency of the PV cell. The resulting short-circuit current 190 density J_{SC}^{QE} is thus an estimation based on two measurements: the *EQE* which is fixed for each PV 191 converter and the spectra $\Phi_{p,\lambda}$ fluctuating in time:

$$J_{SC}^{QE} = q \int_{0}^{\lambda_{g}} \Phi_{p,\lambda} \times EQE \ d\lambda$$
⁽⁷⁾

Now that the spectral response EQE is not ideal anymore but is measured from a real solar cell, the 192 equation (7) gives an estimated value of the short circuit density current J_{SC}^{QE} lower than in the ideal 193 case based on the SQ model (I_{SC}^{SQ}) . This value depends on the real measured spectra at any given time. 194 Then, the measured dark current density-voltage curves $J_{dark}^{meas}(V)$ of the PV converters can be 195 collected by the SMU 2450 from Keithley, and using the superposition principle (Lindholm et al., 196 197 1979; Tarr and Pulfrey, 1980) or more commonly known as the one-diode photovoltaic model, it is possible to deduce the estimated current density-voltage $I^{mod}(V)$ model at any given time of the 198 199 fluctuating spectra:

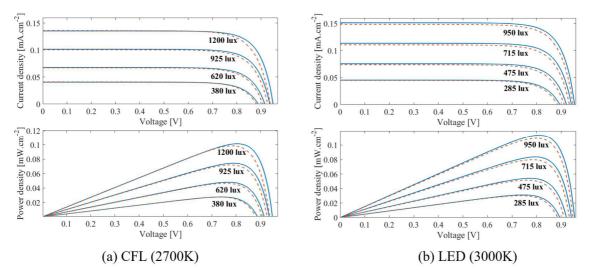
$$J^{mod}(V) = J^{meas}_{dark}(V) + J^{QE}_{SC}$$
(8)

200 As an example, Fig. 3(a) shows the LED spectra of a 300 lux LED 3000K bulb as well as the 201 measured EQE curve of a GaAs solar cell and the current generation of this cell resulting from its 202 absorption of the photon flux. In Fig. 3(b), based on the previous EQE curve and the LED spectra and the $J_{dark}^{meas}(V)$ curve, the estimated $J^{mod}(V)$ is shown as well as the measured $J^{meas}(V)$. In this first 203 example, the current density curve $J^{mod}(V)$, estimated from the developed model, is in good 204 agreement with the experimentally measured $I^{meas}(V)$. In this example, the extracted maximal power 205 values P_{max}^{mod} and P_{max}^{meas} from the model $J^{mod}(V)$ and measured $J^{meas}(V)$, are 30 μ W/cm² and 206 207 $31 \,\mu$ W/cm², respectively, with a difference of about 3 %.



(a) (b) Fig.3. (a) spectra of a 300 lux LED 3000K bulb and the same spectra modulated by the measured external quantum efficiency of a GaAs solar cell. (b) the $J_{dark}^{meas}(V)$ curve of the GaAs solar cell in blue dash used to calculate the expected $J^{mod}(V)$ based on (8) in orange dash, compared to the experimentally measured $J^{meas}(V)$.

212 We have used this method with the same GaAs solar cell under single controlled sources light environments, for different sources (CFL and LED) at many different levels of indoor irradiance (from 213 214 200 lux up to 1000 lux), to verify the reliability of the one-diode photovoltaic model. The characteristics resulting from the model, $I^{mod}(V)$ and the $P^{mod}(V)$, are shown in Fig. 4 and compared 215 to their experimental equivalents, $I^{meas}(V)$ and the $P^{meas}(V)$. The deviation between model results 216 and the experimental measurements is noticeable but minor. With an average error of less than 3 % 217 and never exceeding 5 %, considering the numerous experimental bias possible, these results seem 218 sufficiently accurate to be useful for the calculation of a harvestable power approximation in various 219 220 low irradiance indoor environments.



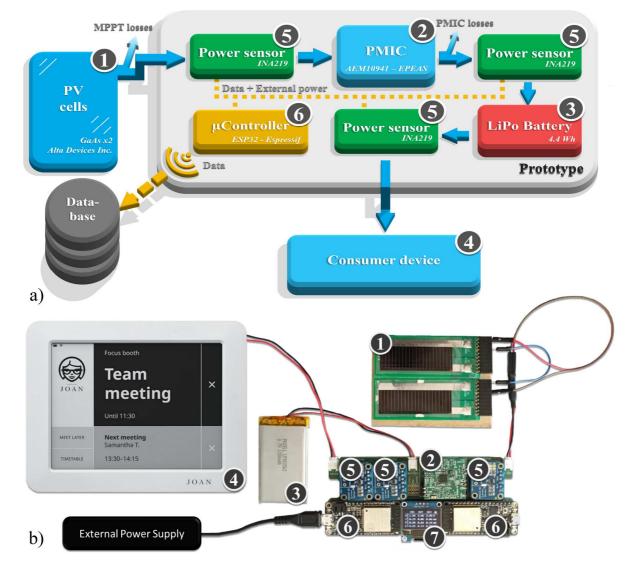
(a) CFL (2700K)
 (b) LED (3000K)
 Fig. 4 Comparison between the calculated J^{mod}-V and the P^{mod}-V (plain blue lines) from the one-diode
 photovoltaic model and the corresponding experimental characteristics J^{meas}-V and the P^{meas}-V (dotted orange
 lines) of a GaAs solar cell for different illuminance under (a) a CFL light source and (b) a LED light source.

As stated previously in this paper, the lack of standards to rely on makes studying in the field of indoor PV more complex. Consequently, it is necessary to find a method to evaluate the produced energy based on the analysis of a fluctuating mix of natural and artificial light environments. The next paragraph will demonstrate the reliability of the simple one-diode photovoltaic model described beforehand to calculate the harvestable energy in real-life indoor conditions, even for several days.

4. The model applied in real conditions for several days

The ultimate purpose of this study is to establish a model to calculate, as precisely as possible, the level of harvestable energy in a real indoor environment for an extended period. Therefore, it is necessary to test the model under real-life conditions, observing the light environment over time to know the variations in its composition and to compare the calculated results to experimental results. A complete energy harvesting prototype, shown in Fig. 5, has been developed to validate the developed model experimentally in real-life environments. This prototype is based on two GaAs thin-film solar cells providing electrical energy to the energy storage device (here a Lithium-Polymer battery) of a

- 238 consumer device like an e-ink connected device. To extract the maximum power from the solar cells, a
- 239 very low consumption commercial power management integrated circuit (PMIC) from *e-PEAS* has
- been placed between the PV cells and the LiPo battery.



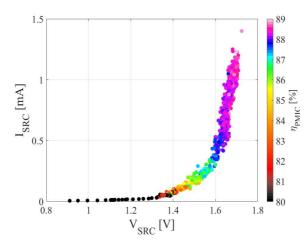
241

242 Fig. 5. a) Schematic of the energy harvesting prototype (PV cells + PMIC + LiPo battery) that has been 243 instrumented by three INA 219 electrical power sensors and two ESP32 microchips to collect the data and send 244 them to a database. Let's note there is a specific external power source that allows the acquisition and 245 transmission of data without affecting the performance of the energy harvester.b) a picture of the described 246 prototype integrating GaAs solar cells (1), a PMIC : an e-peas 'EVK10941M' Mini Evaluation Board based on 247 the 'AEM10941' Solar Energy Harvesting IC (2); a LiPo electrical storage device (3), the e-ink communicating device to power (4), the INA219 power sensors (5), the ESP32 low cost low power microcontroller chips (6) and 248 249 an OLED screen (7).

The used PMIC is based on a max power point tracking (MPPT) algorithm called fractional opencircuit voltage (FOCV). This method relies on getting a sample of the V_{oc} and then applies and holds a fraction of its value to the PV cells or module (Motahhir et al., 2020). Besides not being the most performant in casual energy harvesting situations, such an MPPT algorithm has demonstrated its use of relevance in low light environments (Weddell et al., 2012). Even though this PMIC is adapted for low 255 energy harvesting applications, the losses are not negligible. To include these losses in our model, and 256 to be able to measure the "real" power harvested by the prototype at any time into the LiPo battery, 257 two voltage and current sensing chips INA219 from Texas Instrument have been inserted between the PV cells and the PMIC and between the PMIC and the LiPo. Regarding the classical Lithium Polymer 258 259 (LiPo) battery whom internal resistance is usually less than $100m\Omega$, it has no impact in term of losses when considering the low current level in our application. In addition, a third INA219 has been 260 inserted between the LiPo battery and the consumer device to monitor its consumption. A set of two 261 262 microcontrollers associated with these power sensors allows the acquisition of the power 263 generation/consumption data from the three INA 219, and their recording on a database in the cloud. 264 An external power source is used to power the sensors and the microcontrollers.

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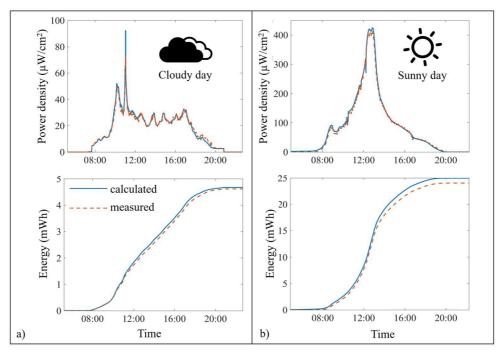
266 The e-peas PMIC Mini Evaluation Board EVK10941M chosen for the prototype uses the fractional 267 open-circuit voltage (FOCV) algorithm. To extract the maximum power from the PV cells, this PMIC algorithm can be configured to apply 70%, 75%, 85%, or 90% of their V_{oc} . In our application, by 268 choosing the fraction of 85%, the MPPT losses due to the optimal fraction of V_{oc} not being exactly 269 270 equal to 85%, are evaluated to be lower than 1% over the whole range of illumination. Regarding the 271 PMIC losses induced by the classical losses of a buck-boost converter, they can vary from 10% to 20% 272 depending on the level of illumination. As can be seen in Fig.6, at low light (and low V_{SRC} et low I_{SRC}), 273 the efficiency of the PMIC is only 80 % while at moderate to high illumination the efficiency is about 274 90%. From the plot of Fig.6, a regressive equation has been added to our model to include the PMIC efficiency η^{PMIC} . 275



276

Fig. 6. Experimental PMIC efficiency η^{PMIC} depending on ligh intensity. These curve depends on the experimental set-up, in our case two GaAs solar cell in series, an epeas based PMIC and a single cell LiPo.

Finally, the purpose of the experiment is to compare the harvestable energy calculated by the model and the real harvested energy measured by the power sensor, the power measurements must be carried out simultaneously with the spectrometer analysis of the light environment to which the prototype is exposed. This experiment has been carried out over 21 days. The results of 2 typical days (sunny and 283 cloudy days) are shown in Fig.7. While the orange dashed line is the experimental harvested power 284 stored into the Lithium Polymer battery measured directly by an INA219, the blue line represents the 285 model calculation results based on one-minute spectra measurement intervals. A qualitative agreement 286 between the model calculation of power and energy harvesting and the real usable power generated and energy transferred to the prototype battery can be observed. The mean absolute percentage error 287 288 (MAPE) between the model curve and the experimental power curve of each of the 21 days is lower 289 than 6%. These very good results are comforting the fact that our model and methods are reliable 290 enough to be an interesting tool for researchers and engineers conceiving indoor micro source elements 291 for IoT applications or consumer devices.



292 293

Fig. 7. model's power density and energy calculations (plain blue) and experimentally measured power-density
and energy (dash orange) generated from the GaAs solar cell in a real-life indoor environment harvested into the
Lithium Polymer storage device for a) a cloudy day and b) a sunny day.

The 6% of error are potentially due to several factors: i) the MPPT losses ii) the LiPo battery losses, iii) the reliability of the low-cost INA219, iv) the reliability of our model which has been taken as simple as possible without taking into account potential variation of R_{sh} and R_s with light intensity,

300 v) the small effect of temperature in indoor Environnement, vi) and of course the experimental setup.

301

These results obtained after 21 days of observation of the office's real lighting environment show that the model makes it possible to determine the level of harvestable energy per surface unit quite accurately, even if there is still room for improvement. It is then possible to determine, based on these 21 days of observation, the harvesting surface area or the number of PV cells required in this environment to compensate for the energy needs of an electronic device fully. For example, a classical wireless e-ink dashboard, as the one used in this study, depending on its size and the significance of its sleeping mode, consumes about 10 mW on average. In such a case, a preliminary extrapolation shows that 14x14 cm² of similar solar cells would be sufficient to supply it enough power to make it energetically autonomous.

311 5. Conclusion

In summary, the simple model presented applying the superposition principle, based on the 312 combination of the measured optical EQE and electrical J^{meas}_{dark}-V of GaAs PV cell in the dark, 313 combined with the spectral measurements of real-life indoor environments, has demonstrated the 314 ability to calculate the potentially harvestable energy in the environment that is being studied. Using 315 316 an energy-harvesting prototype installed in the environment studied by the spectrometer feeding the 317 developed model allowed to confront results from the model to actual power and energy harvest. The 318 confrontation result corroborates the ability of the proposed model to calculate the harvestable energy with an error lower than 6 % for the 21 days of the test. In a more practical sense, this paper shows 319 320 that in real-life indoor environments, a module based on PV cells similar to Alta Devices Inc. GaAs 321 PV solar cells and smaller than a third of a sheet of paper (A4 format) is enough to make devices 322 consuming about 10 mW.

- 323 We believe that the method presented in this article will be helpful to engineers and researchers
- 324 attempting to overcome the various challenges toward the accurate design of energy harvesting
- 325 devices in the future.

326 Declaration of Competing Interest

327 The authors declare no conflict of interest.

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